

<b>SANYO</b>	No.4667	<b>2SB1527</b>
		PNP Epitaxial Planar Silicon Transistor

**Compact Motor Driver Applications**

**Features**

- Low saturation voltage.
- Contains a diode between collector and emitter.
- Contains a bias resistor between base and emitter.
- Large current capacity.
- Compact package making it easy to realize high-density, small-sized hybrid ICs.

**Absolute Maximum Ratings at Ta = 25°C**

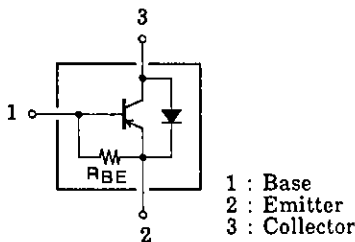
			unit
Collector-to-Base Voltage	V <sub>CB0</sub>	-20	V
Collector-to-Emitter Voltage	V <sub>CEO</sub>	-15	V
Emitter-to-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	I <sub>C</sub>	-0.8	A
Collector Current(Pulse)	I <sub>CP</sub>	-2	A
Collector Dissipation	P <sub>C</sub>	200	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

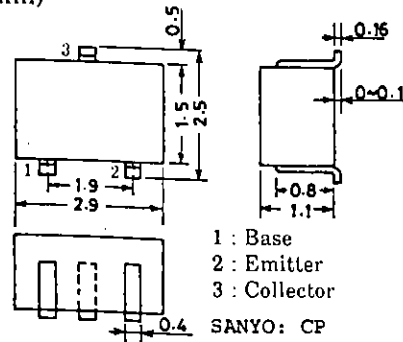
		min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = -15V, I <sub>E</sub> = 0		-1.0	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = -2V, I <sub>C</sub> = -0.5A		70	
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = -2V, I <sub>C</sub> = -0.5A		250	MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V, f = 1MHz		30	pF
C-E Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -500mA, I <sub>B</sub> = -10mA		-0.2	V
B-E Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -500mA, I <sub>B</sub> = -10mA		-0.95	V
C-B Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -10μA, I <sub>E</sub> = 0		-20	V
C-E Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -10mA, R <sub>BE</sub> = ∞		-15	V
Diode Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = -0.5A		-1.5	V
Base-to-Emitter Resistance	R <sub>BE</sub>			1.0	kΩ

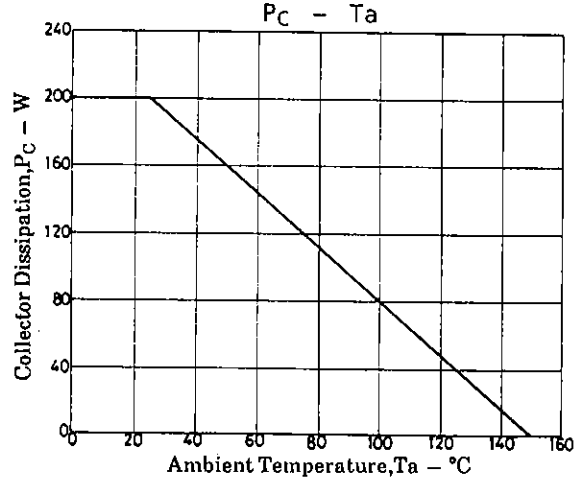
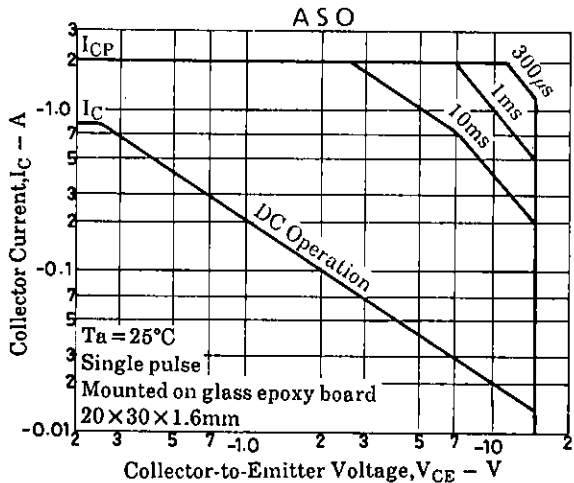
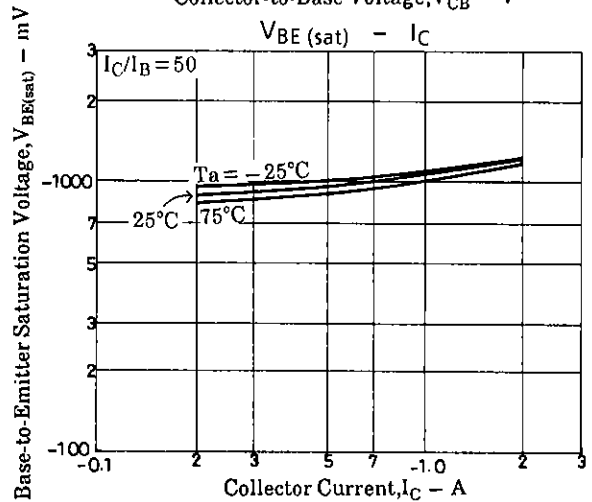
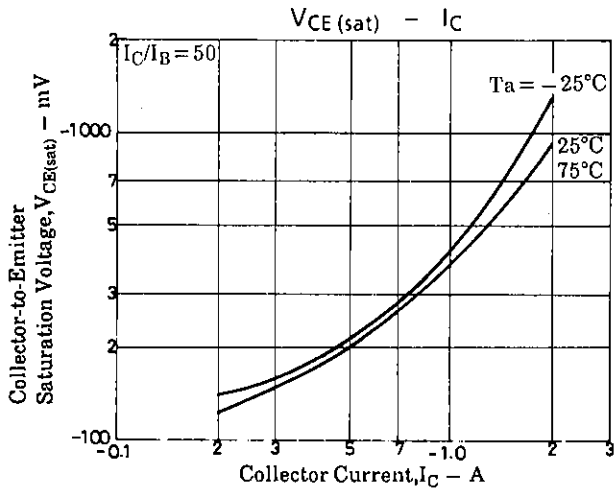
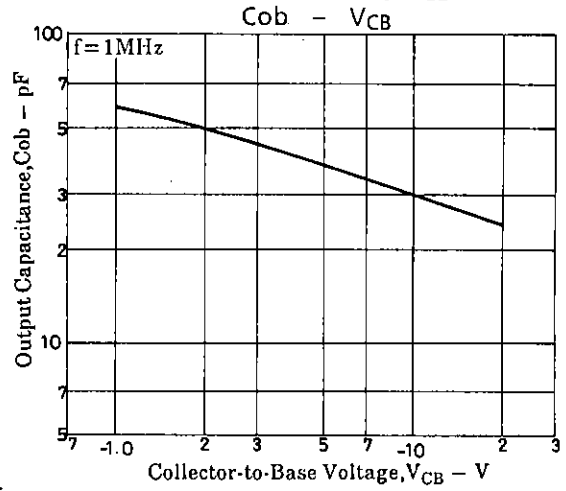
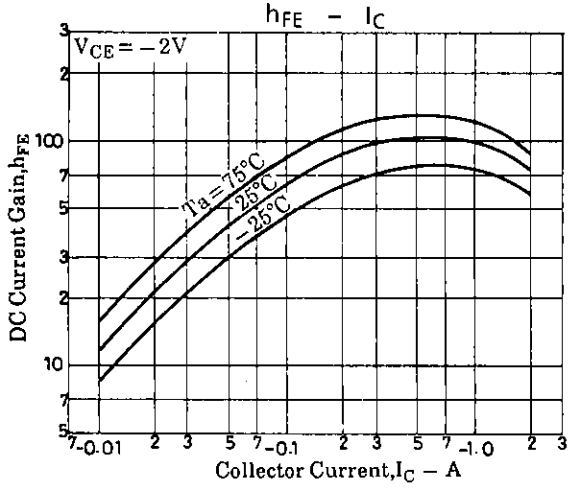
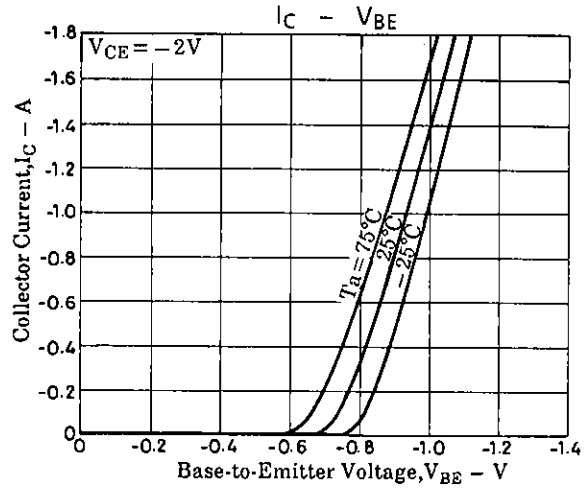
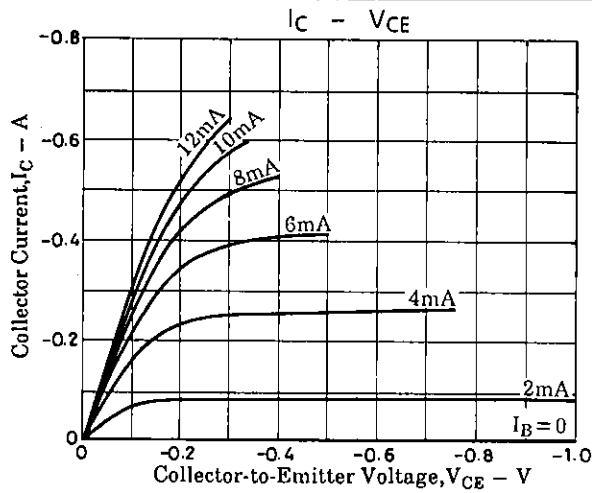
Marking : NS

**Electrical Connection**



**Package Dimensions 2018B**  
(unit : mm)





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